MB2M-MB10M

单向硅整流桥堆

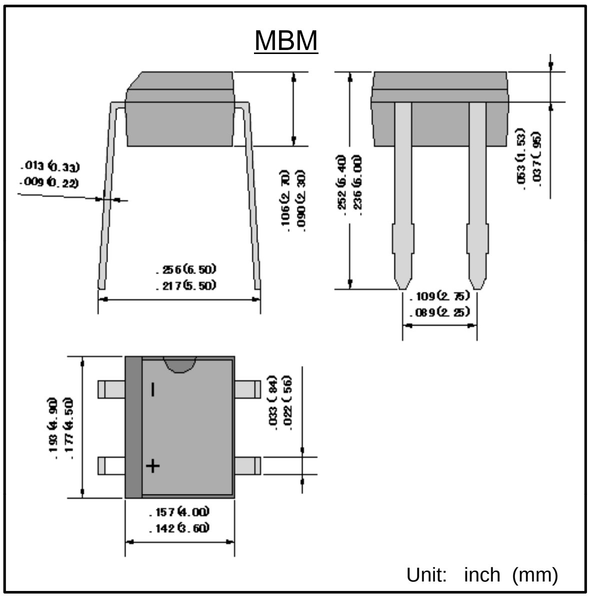
反向电压 200 ~ 1000 V

正向电流 0.5 A

Single phase Silicon Bridge Rectifiers

Reverse Voltage 200 ~ 1000 V

Forward Current 0.5 A



特征 Features

- 反向漏电流低   Low reverse leakage
- 正向浪涌承受能力强   High forward surge capability
- 高温焊接保证 High temperature soldering guaranteed:
- 玻璃钝化芯片 Glass passivated chip

  260℃/10 秒 260℃/10seconds
- 引线和管体皆符合RoHS标准 。

  Lead and body according with RoHS standard

机械数据   Mechanical Data

- 封装: MBM 塑料封装 Case: MBM Molded plastic
- 极性: 标记模压或印于本体

  Polarity: Symbols molded or marked on body
- 安装位置: 任意   Mounting Position: Any

最大值和特性   TA = 25℃ 除非另有规定。

Maximum Ratings & Characteristics

Ratings at 25℃ ambient temperature unless otherwise specified.

参数 Parameter	符号 Symbols	MB2M	MB4M	MB6M	MB8M	MB10M	单位 Unit
最大可重复峰值反向电压 Maximum repetitive peak reverse voltage	V_{RRM}	200	400	600	800	1000	V
最大均方根电压 Maximum RMS voltage	V_{RMS}	140	280	420	560	700	V
最大直流阻断电压 Maximum DC blocking voltage	V_{DC}	200	400	600	800	1000	V
最大正向平均整流电流 Maximum average forward rectified current	$I_{F(AV)}$	0.5					A
正向不重复浪涌电流 10 ms单一正弦半波 Non-repetitive peak forward surge current 10 ms singlehalf sine-wave	I_{FSM}	35					A
最大正向电压 @IF=0.4A Maximum forward voltage	V_F	1.0					V
最大反向电流 @V_{DC} Maximum reverse current	I_R	5					μA
典型热阻 Typical thermal resistance (Note 1)	RθJA	85					℃/W
	RθJL	20					
工作结温和存储温度 Operating junction and storage temperature rang	Tj, TSTG	-55 --- +150					℃

备注 Note:

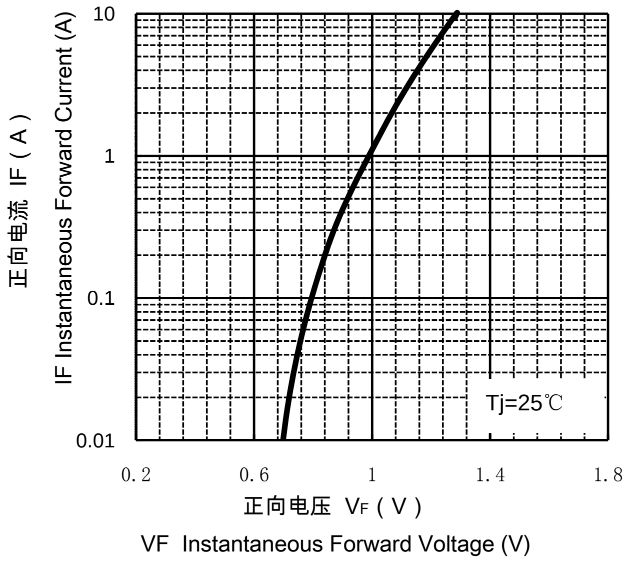
1) 安装在PCB板上，从PN结到环境的热阻。

1) Thermal resistance from junction to ambient , PCB mounted.

特性曲线　Characteristic Curves

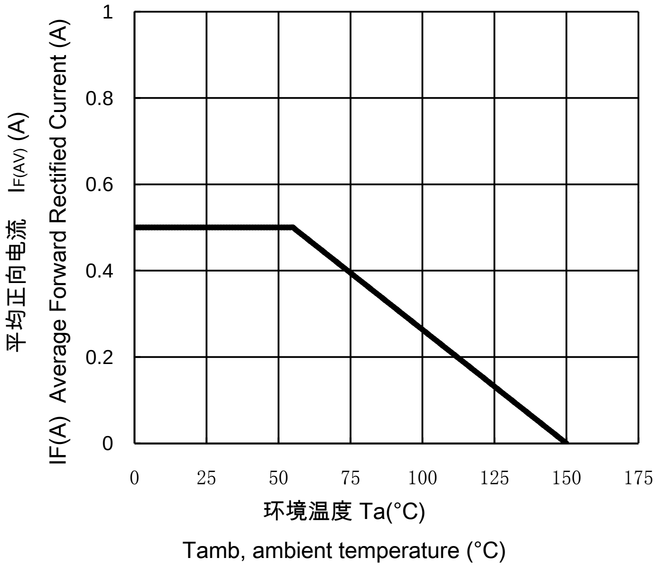
正向特性曲线（典型值）

TYPICAL FORWARD CHARACTERISTIC



正向电流降额曲线

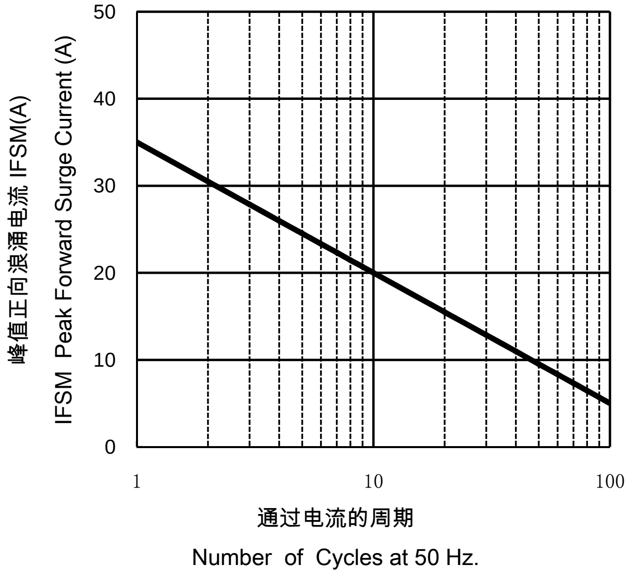
FORWARD CURRENT DERATING CURVE



浪涌特性曲线（最大值）

MAXIMUM NON REPETITIVE

PEAK FORWARD SURGE CURRENT



反向特性曲线

Typical Reverse Characteristics